2SC5469

Silicon NPN Triple Diffused Character Display Horizntal Deflection Output

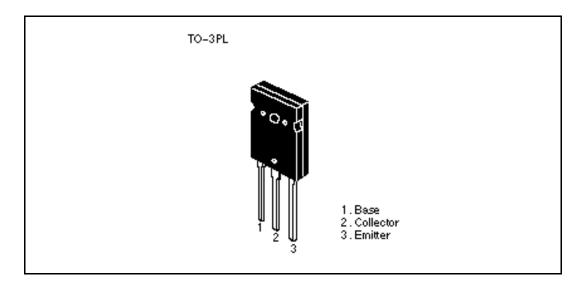
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3rd. Edition December 1997 Target Specification

Features

- High breakdown voltage $V_{CBO} = 1500 \text{ V}$
- High speed switching $t_{\rm f} = 0.15 \; \mu sec \; (typ.) \; \; at \; f_{\rm H} = 64 kHz \label{eq:higher_fit}$

Outline





2SC5469

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	1500	V
Collector to emitter voltage	V_{CEO}	700	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	Ic	15	A
Collector peak current	i _{c(peak)}	30	A
Collector power dissipation	P _c ^{Note1}	125	W
Junction temperature	Тј	150	°C
Storage temperature	Tstg	-55 to +150	°C

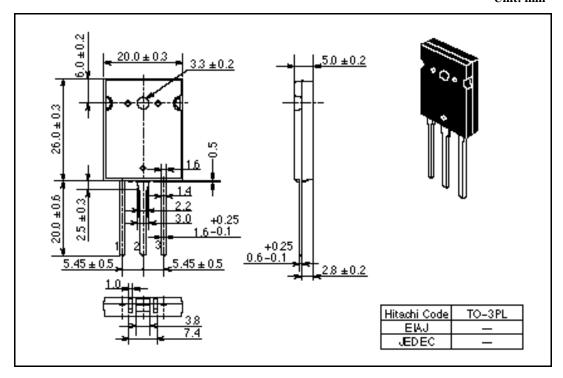
Note: 1. Value at Tc = 25°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	700	_	_	V	$I_{\rm C}$ = 10mA, $R_{\rm BE}$ =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	_	_	V	$I_{E} = 10 \text{mA}, I_{C} = 0$
Collector cutoff current	I _{CES}	_	_	500	μΑ	$V_{CE} = 1500V, R_{BE} = 0$
DC current transfer ratio	h _{FE1}	10	_	40		$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{A}$
DC current transfer ratio	h _{FE2}	3.5	_	6.5		$V_{CE} = 5 \text{ V}, I_{C} = 8 \text{A}$
Collector to emitter saturation voltage	V _{CE(sat)}	_	_	5	V	$I_{\rm C} = 10A, I_{\rm B} = 3A$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	_	1.5	V	$I_C = 10A$, $I_B = 3A$
Fall time	t,	_	0.2	0.4	μs	$I_{CP} = 7A, I_{B1} = 2.8A$ $f_{H} = 31.5kHz$
Fall time	t,	_	0.15	_	μs	$I_{CP} = 7A, I_{B1} = 1.8A$ $f_{H} = 64kHz$

Package Dimensions

Unit: mm



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